



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

2SC536 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 400 mW ($T_{amb}=25^{\circ}C$)

Collector current

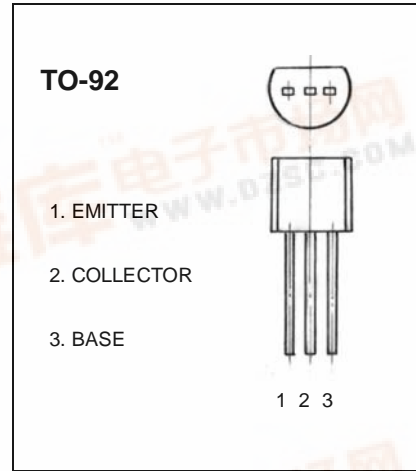
I_{CM} : 100 mA

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	30			V
Emitter-Base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=35V, I_E=0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			1	μA
DC current gain	h_{FE}	$V_{CE}=6V, I_C=1mA$	60		960	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.5	V
Transition frequency	f_T	$V_{CE}=6V, I_C=1mA$		100		MHz
Collector output capacitance	C_{ob}	$V_{CE}=6V, f=1MHz$		3.5		pF

CLASSIFICATION OF h_{FE}

Rank	D	E	F	G	H
Range	60-120	100-200	160-320	280-560	480-960